

Product Overview

FCMT180N65S3: Power MOSFET, N-Channel, SUPERFET® III, Easy Drive, 650 V, 17 A, 180 mΩ, POWER88

For complete documentation, see the data sheet.

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction(SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SUPERFET III MOSFET is very suitable for the switching power applications such as server/telecom power, adapter and solar inverter applications. The Power88 package is an ultra-slim surface-mount package (1mm high) with a low profile and small footprint (8 * 8 mm²). SUPERFET III MOSFET in a Power88 package offers excellent switching performance due to lower parasitic source inductance and separated power and drive sources. Power88 offers Moisture Sensitivity Level 1(MSL 1).

Features

- 700 V @ T_J = 150 °C
- Leadless Ultra-thin SMD package
- Kelvin contact
- Ultra Low Gate Charge (Typ. Q_g = 33 nC)
- Low Effective Output Capacitance (Typ. C_{oss}(eff.) = 305 pF)
- Optimized Capacitance
- Typ. R_{DS(on)} = 152 mΩ
- 100% Avalanche Tested
- RoHS Compliant
- Moisture Sensitivity Level 1 guarantee

For more features, see the data sheet

Benefits

- Higher system reliability at low temperature operation
- High power density
- Low gate noise and switching loss
- Low switching loss
- Low switching loss
- Lower peak V_{ds} and lower V_{gs} oscillation

Applications

- Telecommunication
- Cloud system
- Industrial

End Products

- Telecom power
- Server power
- LED Lighting
- Adapter

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V _{(BR)DSS} Min (V)	V _{GS} Max (V)	V _{GS(th)} Max (V)	I _D Max (A)	P _D Max (W)	R _{DS(on)} Max @ V _{GS} = 2.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 4.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 10 V (mΩ)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	C _{iss} Typ (pF)	Package Type
FCMT180N65S3	0.9256	Pb-free Halide free	Active	N-Channel	Single	650	30	4.5	17	139	-	-	180	-	33	1350	PQFN-4

For more information please contact your local sales support at www.onsemi.com.

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